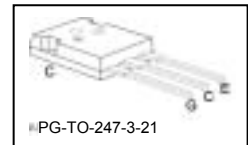
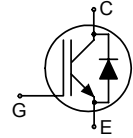


Low Loss DuoPack : IGBT in TrenchStop® and Fieldstop technology with anti-parallel diode

Features:

- 1.1V Forward voltage of antiparallel diode
- TrenchStop® and Fieldstop technology for 900 V applications offers :
 - very tight parameter distribution
 - high ruggedness, temperature stable behavior
 - easy parallel switching capability due to positive temperature coefficient in $V_{CE(sat)}$
- Low EMI
- Qualified according to JEDEC¹ for target applications
- Application specific optimisation of inverse diode
- Pb-free lead plating; RoHS compliant



Applications:

- Microwave Oven
- Soft Switching Applications for ZCS

Type	V_{CE}	I_C	$V_{CE(sat)}, T_j=25^\circ\text{C}$	$T_{j,max}$	Marking	Package
IHW30N90T	900V	30A	1.5V	175°C	H30T90	PG-TO-247-3-21

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CE}	900	V
DC collector current	I_C	60 30	A
$T_C = 25^\circ\text{C}$			
$T_C = 100^\circ\text{C}$			
Pulsed collector current, t_p limited by T_{jmax}	I_{Cpuls}	900	
Turn off safe operating area $V_{CE} \leq 1200\text{V}$, $T_j \leq 150^\circ\text{C}$	-	90	
Diode forward current	I_F	23 13	
$T_C = 25^\circ\text{C}$			
$T_C = 100^\circ\text{C}$			
Diode pulsed current, t_p limited by T_{jmax}	I_{Fpuls}	36	
Gate-emitter voltage	V_{GE}	± 20	V
Transient Gate-emitter voltage ($t_p < 5\text{ ms}$)		± 25	
Power dissipation, $T_C = 25^\circ\text{C}$	P_{tot}	428	W
Operating junction temperature	T_j	-40...+175	°C
Storage temperature	T_{stg}	-55...+175	°C
Soldering temperature, 1.6mm (0.063 in.) from case for 10s	-	260	

¹ J-STD-020 and JESD-022

Thermal Resistance

Parameter	Symbol	Conditions	Max. Value	Unit
Characteristic				
IGBT thermal resistance, junction – case	R_{thJC}		0.35	K/W
Diode thermal resistance, junction – case	R_{thJCD}		1.1	
Thermal resistance, junction – ambient	R_{thJA}		40	

Electrical Characteristic, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	Typ.	max.	
Static Characteristic						
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE}=0V, I_C=500\mu A$	900	-	-	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$V_{GE} = 15V, I_C=30A$				
		$T_j=25^{\circ}C$	-	1.5	1.7	
		$T_j=150^{\circ}C$	-	1.7	-	
		$T_j=175^{\circ}C$	-	1.8	-	
Diode forward voltage	V_F	$V_{GE}=0V, I_F=10A$				
		$T_j=25^{\circ}C$	-	1.1	1.3	
		$T_j=150^{\circ}C$	-	1.0	-	
		$T_j=175^{\circ}C$	-	1.0	-	
Gate-emitter threshold voltage	$V_{GE(th)}$	$I_C=150\mu A, V_{CE}=V_{GE}$	4.6	5.3	6	
Zero gate voltage collector current	I_{CES}	$V_{CE}=900V,$ $V_{GE}=0V$				μA
		$T_j=25^{\circ}C$	-	-	250	
		$T_j=150^{\circ}C$	-	-	2500	
Gate-emitter leakage current	I_{GES}	$V_{CE}=0V, V_{GE}=20V$	-	-	600	nA
Transconductance	g_{fs}	$V_{CE}=20V, I_C=20A$	-	26	-	S

Dynamic Characteristic

Input capacitance	C_{iss}	$V_{CE}=25V,$ $V_{GE}=0V,$ $f=1\text{MHz}$	-	2617	-	pF
Output capacitance	C_{oss}		-	96	-	
Reverse transfer capacitance	C_{rss}		-	38	-	
Gate charge	Q_{Gate}	$V_{CC}=720V, I_C=30A$ $V_{GE}=15V$	-	280	-	nC
Internal emitter inductance measured 5mm (0.197 in.) from case	L_E		-	13	-	nH

Switching Characteristic, Inductive Load, at $T_j=25\text{ }^{\circ}\text{C}$

Parameter	Symbol	Conditions	Value			Unit
			min.	Typ.	max.	
IGBT Characteristic						
Turn-on delay time	$t_{d(on)}$	$T_j=25^{\circ}\text{C}$, $V_{CC}=600\text{V}$, $I_C=30\text{A}$, $V_{GE}=0/15\text{V}$, $R_G=15\Omega$,	-	45	-	ns
Rise time	t_r		-	26	-	
Turn-off delay time	$t_{d(off)}$		-	556	-	
Fall time	t_f		-	29	-	
Turn-on energy	E_{on}		-	-	-	mJ
Turn-off energy	E_{off}		-	1.8	-	
Total switching energy	E_{ts}		-	1.8	-	

Switching Characteristic, Inductive Load, at $T_j=175\text{ }^{\circ}\text{C}$

Parameter	Symbol	Conditions	Value			Unit
			min.	Typ.	max.	
IGBT Characteristic						
Turn-on delay time	$t_{d(on)}$	$T_j=175^{\circ}\text{C}$ $V_{CC}=600\text{V}$, $I_C=30\text{A}$, $V_{GE}=0/15\text{V}$, $R_G=15\Omega$	-	44	-	ns
Rise time	t_r		-	38	-	
Turn-off delay time	$t_{d(off)}$		-	650	-	
Fall time	t_f		-	41	-	
Turn-on energy	E_{on}		-	-	-	mJ
Turn-off energy	E_{off}		-	2.4	-	
Total switching energy	E_{ts}		-	2.4	-	

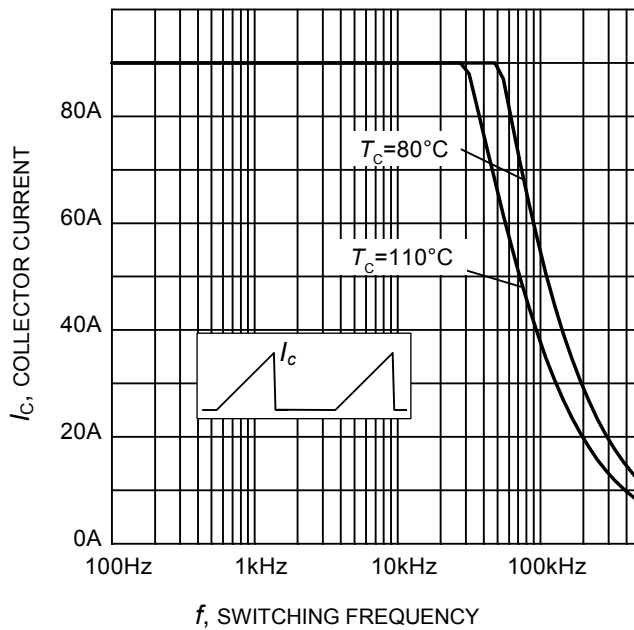


Figure 1. Collector current as a function of switching frequency for triangular current ($E_{on} = 0$, hard turn-off)
($T_j \leq 175^\circ\text{C}$, $D = 0.5$, $V_{CE} = 600\text{V}$, $V_{GE} = 0/+15\text{V}$, $R_G = 15\Omega$)

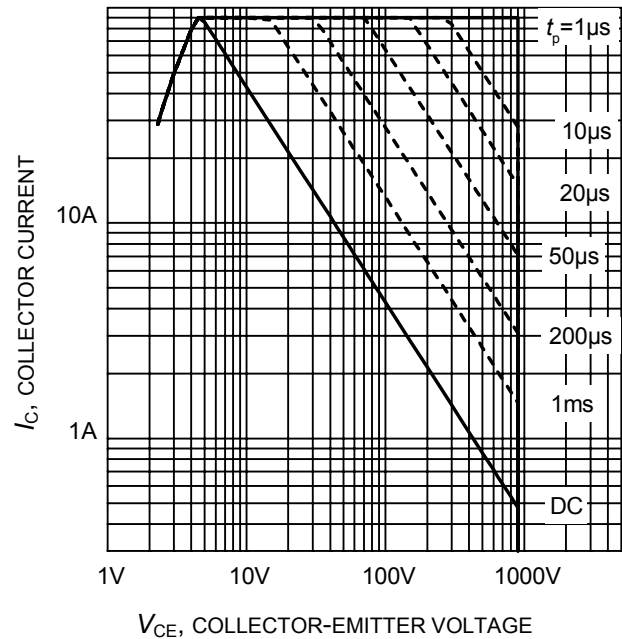


Figure 2. IGBT Safe operating area
($D = 0$, $T_C = 25^\circ\text{C}$, $T_j \leq 175^\circ\text{C}$; $V_{GE} = 15\text{V}$)

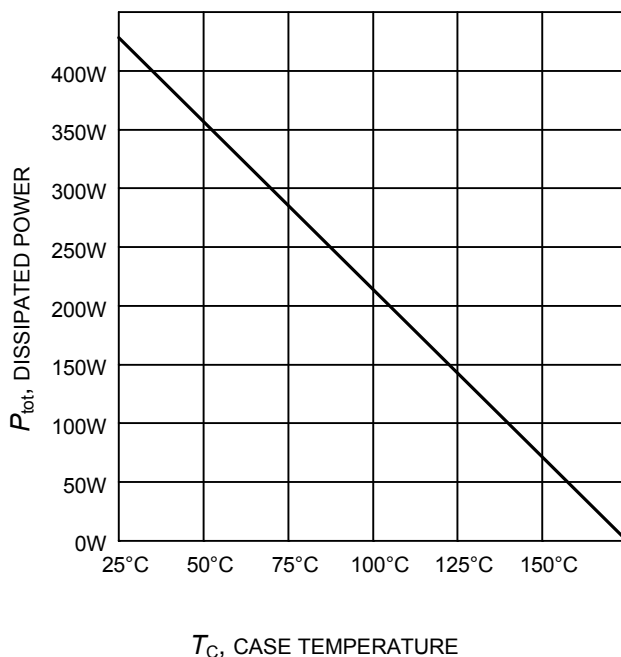


Figure 3. Power dissipation as a function of case temperature
($T_j \leq 175^\circ\text{C}$)

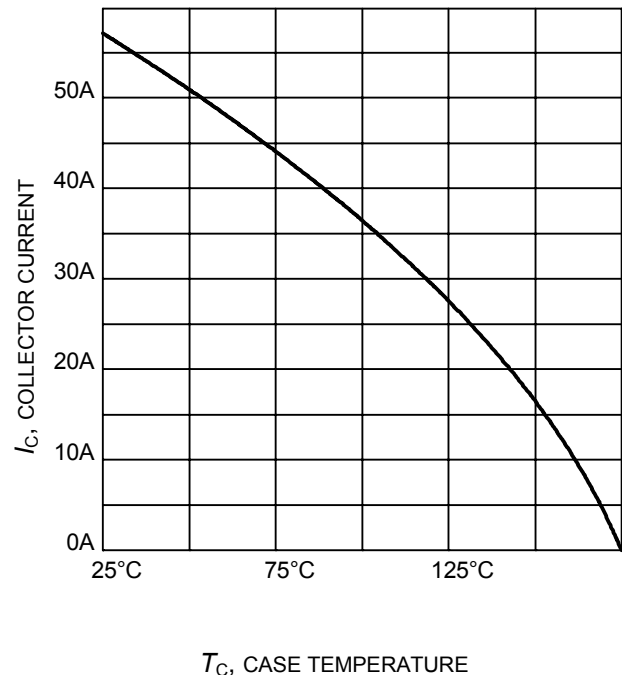


Figure 4. Collector current as a function of case temperature
($V_{GE} \geq 15\text{V}$, $T_j \leq 175^\circ\text{C}$)

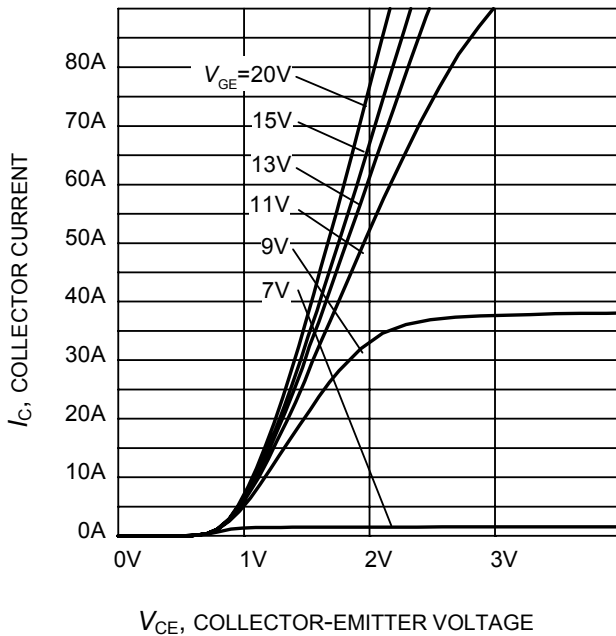


Figure 5. Typical output characteristic
($T_j = 25^\circ\text{C}$)

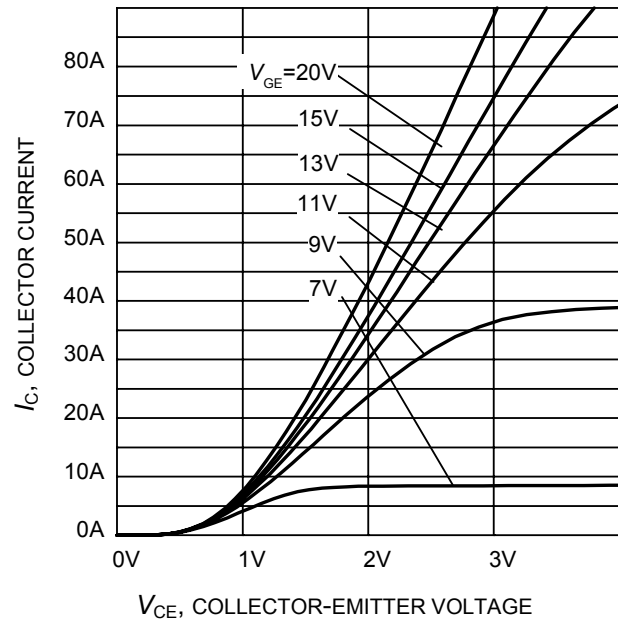


Figure 6. Typical output characteristic
($T_j = 175^\circ\text{C}$)

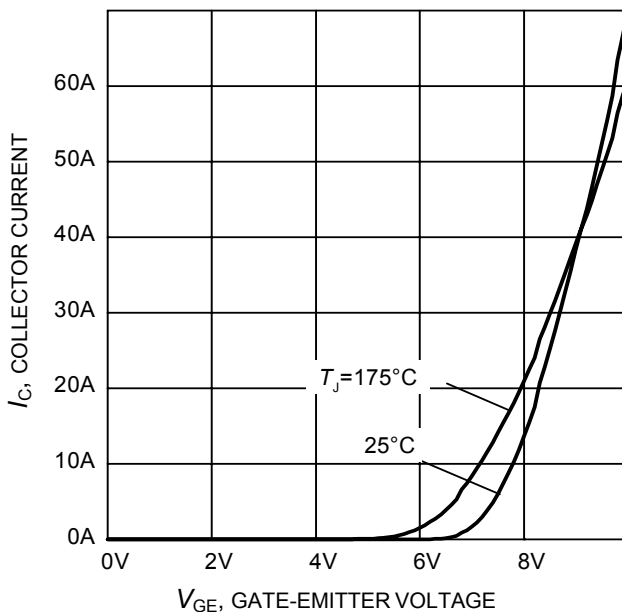


Figure 7. Typical transfer characteristic
($V_{CE}=20\text{V}$)

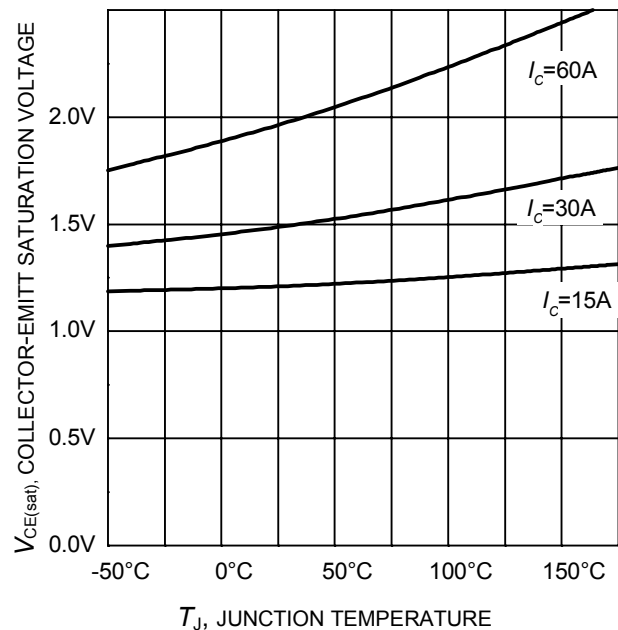


Figure 8. Typical collector-emitter saturation voltage as a function of junction temperature
($V_{GE} = 15\text{V}$)

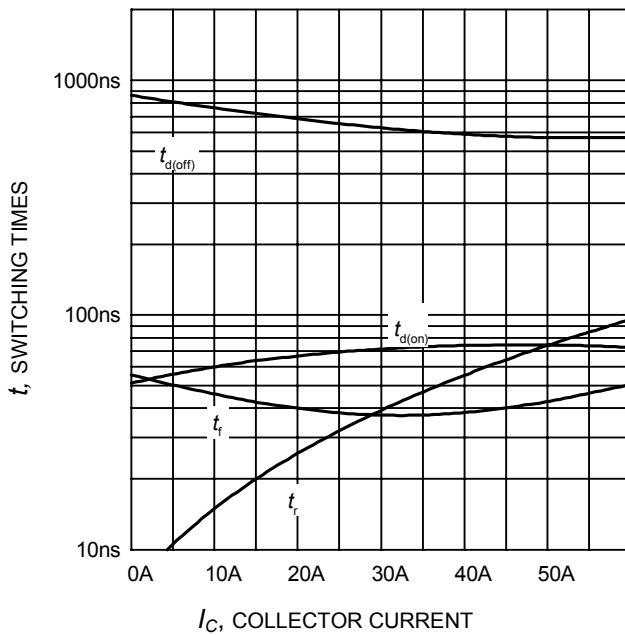


Figure 9. Typical switching times as a function of collector current
(inductive load, $T_J=175^\circ\text{C}$, $V_{CE}=600\text{V}$, $V_{GE}=0/15\text{V}$, $R_G=15\Omega$, Dynamic test circuit in Figure E)

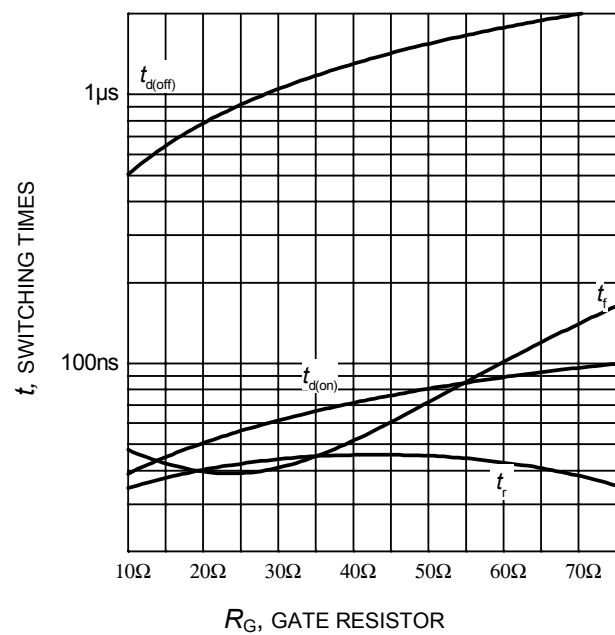


Figure 10. Typical switching times as a function of gate resistor
(inductive load, $T_J=175^\circ\text{C}$, $V_{CE}=600\text{V}$, $V_{GE}=0/15\text{V}$, $I_C=30\text{A}$, Dynamic test circuit in Figure E)

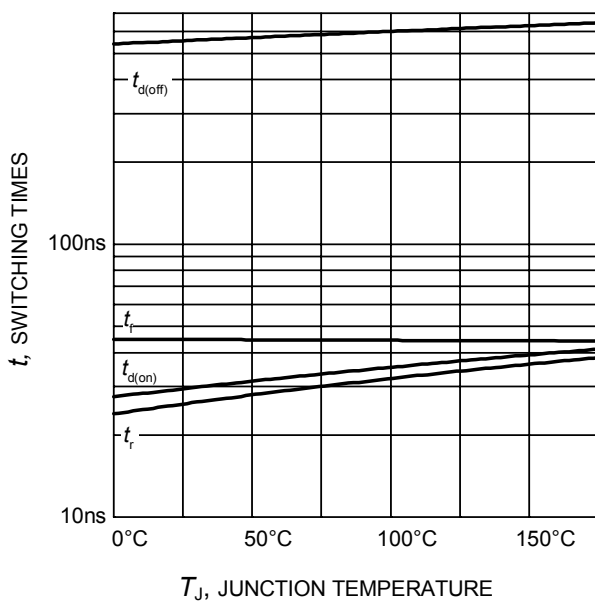


Figure 11. Typical switching times as a function of junction temperature
(inductive load, $V_{CE}=600\text{V}$, $V_{GE}=0/15\text{V}$, $I_C=30\text{A}$, $R_G=15\Omega$, Dynamic test circuit in Figure E)

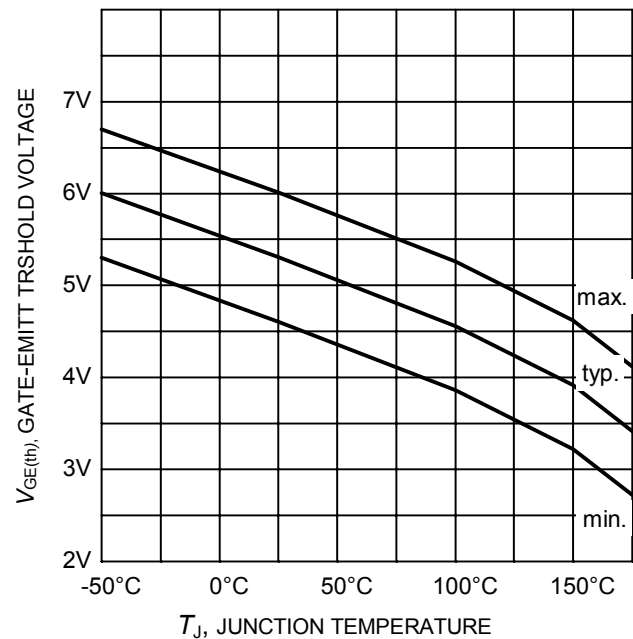


Figure 12. Gate-emitter threshold voltage as a function of junction temperature
($I_C = 0.3\text{mA}$)

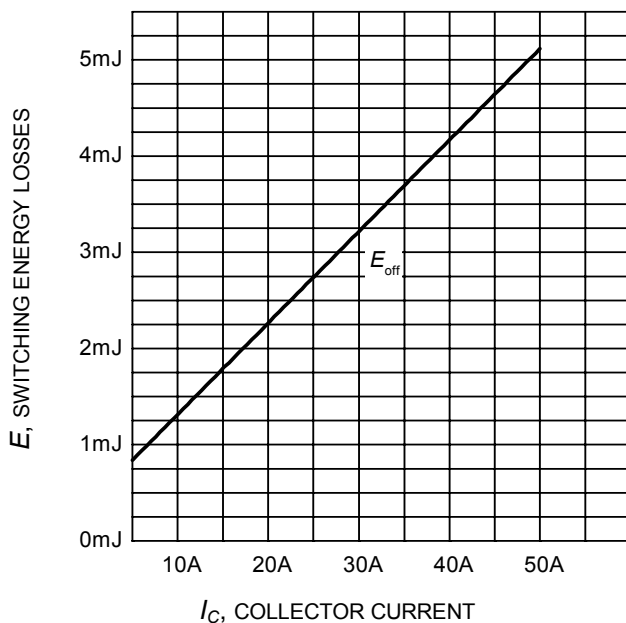


Figure 13. Typical switching energy losses as a function of collector current
(inductive load, $T_J=175^\circ\text{C}$, $V_{CE}=600\text{V}$, $V_{GE}=0/15\text{V}$, $R_G=15\Omega$, Dynamic test circuit in Figure E)

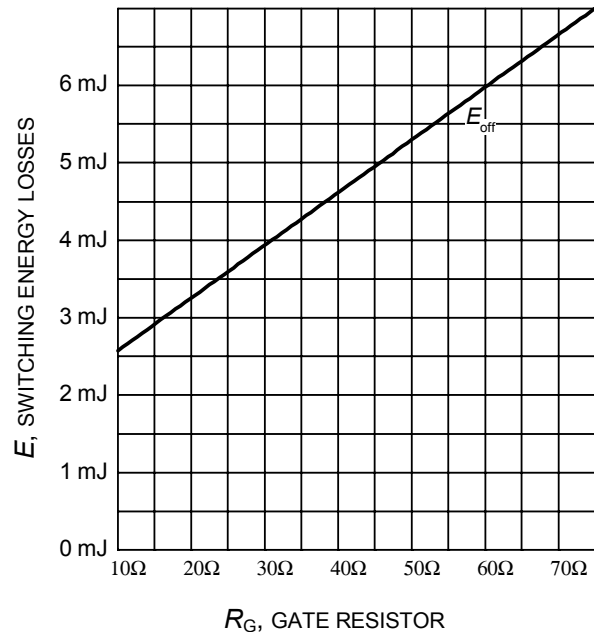


Figure 14. Typical switching energy losses as a function of gate resistor
(inductive load, $T_J=175^\circ\text{C}$, $V_{CE}=600\text{V}$, $V_{GE}=0/15\text{V}$, $I_C=30\text{A}$, Dynamic test circuit in Figure E)

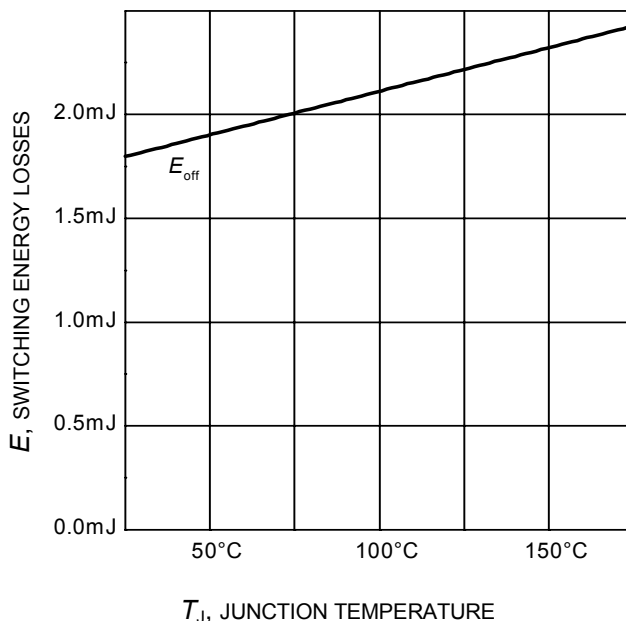


Figure 15. Typical switching energy losses as a function of junction temperature
(inductive load, $V_{CE}=600\text{V}$, $V_{GE}=0/15\text{V}$, $I_C=30\text{A}$, $R_G=15\Omega$, Dynamic test circuit in Figure E)

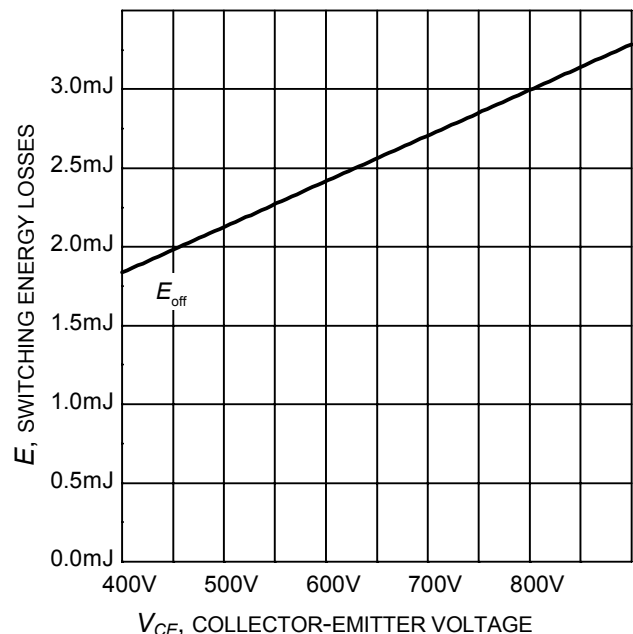


Figure 16. Typical switching energy losses as a function of collector emitter voltage
(inductive load, $T_J=175^\circ\text{C}$, $V_{GE}=0/15\text{V}$, $I_C=30\text{A}$, $R_G=15\Omega$, Dynamic test circuit in Figure E)

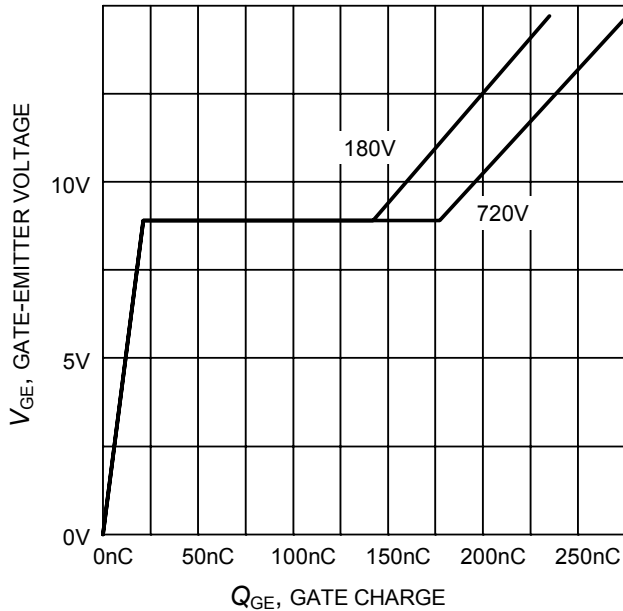


Figure 17. Typical gate charge
($I_C=30\text{ A}$)

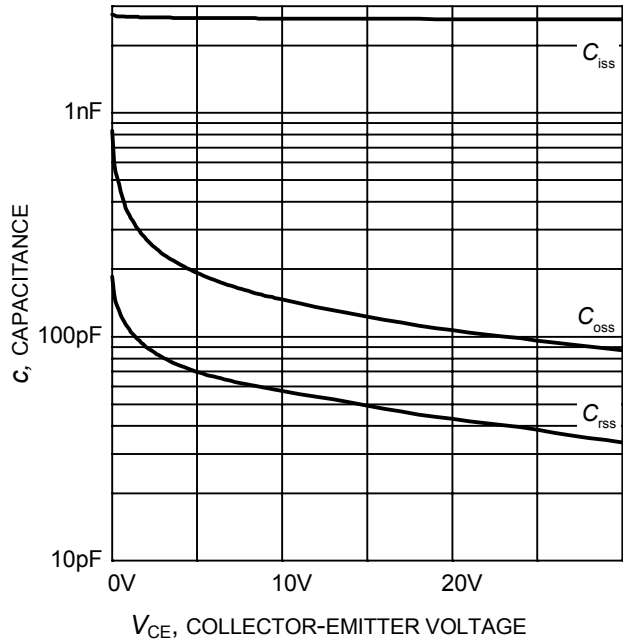


Figure 18. Typical capacitance as a function of collector-emitter voltage
($V_{GE}=0\text{V}$, $f=1\text{ MHz}$)

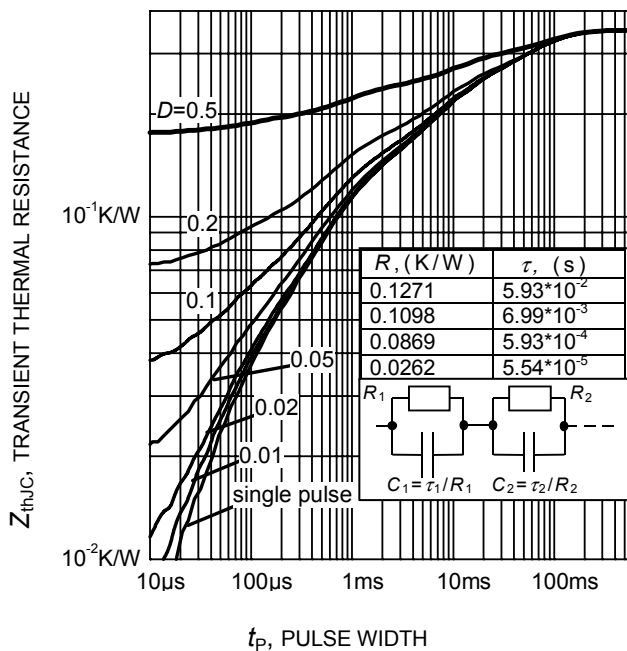


Figure 19. IGBT transient thermal resistance
($D = t_p / T$)

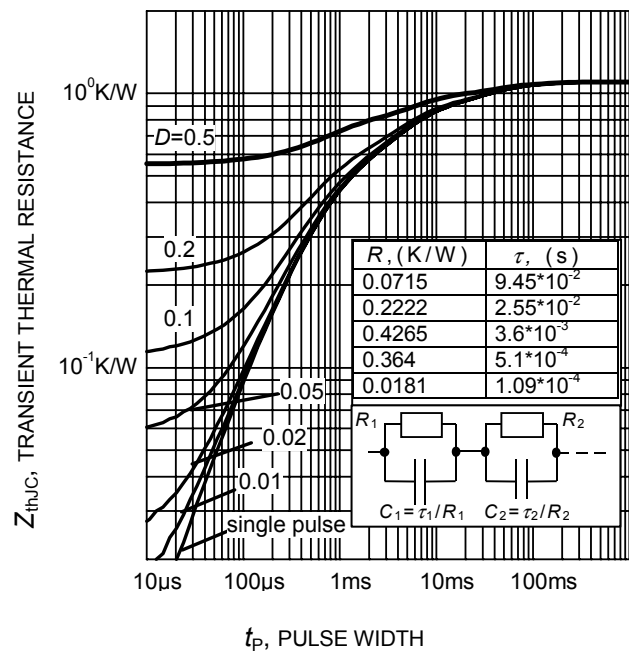


Figure 20. Typical Diode transient thermal impedance as a function of pulse width
($D=t_p/T$)

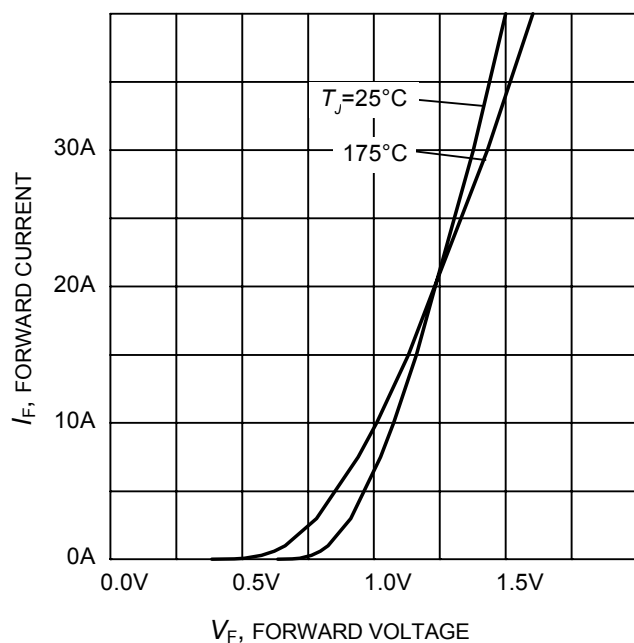


Figure 21. Typical diode forward current as a function of forward voltage

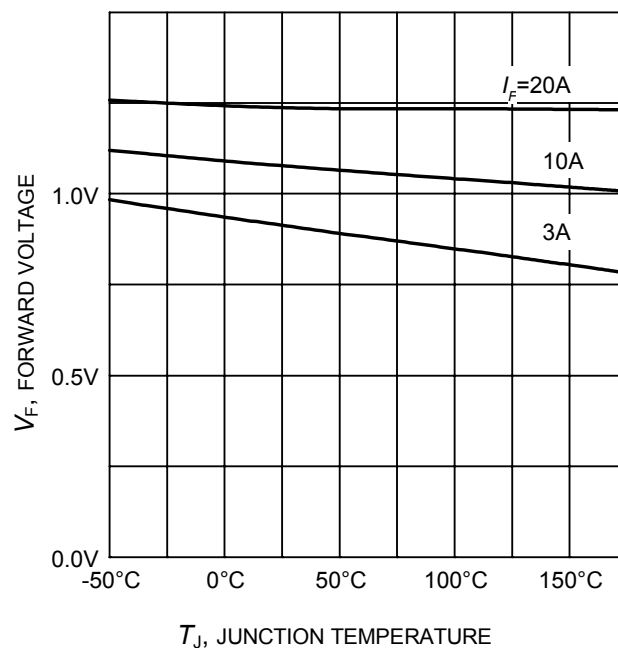
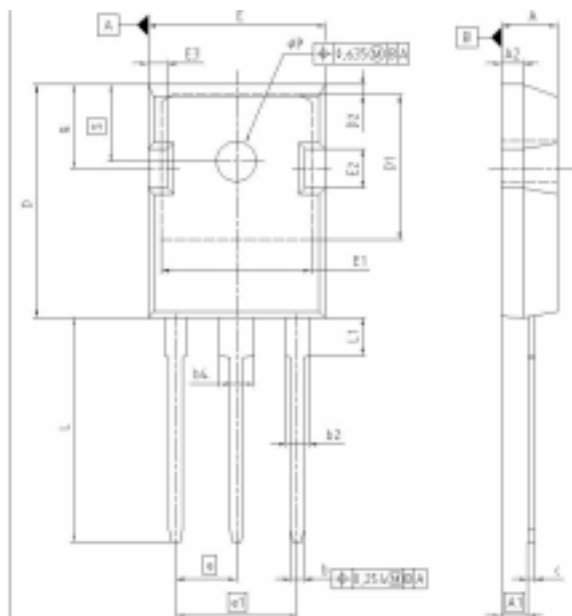


Figure 22. Typical diode forward voltage as a function of junction temperature

PG-TO247-3-21



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.905	5.157	0.193	0.203
A1	2.273	2.527	0.090	0.099
A2	1.653	2.107	0.075	0.081
b	1.073	1.327	0.047	0.052
b2	1.903	2.506	0.075	0.099
b4	2.870	3.454	0.113	0.136
c	0.549	0.752	0.024	0.030
D	29.823	24.077	0.820	0.890
D1	17.323	17.831	0.682	0.702
D2	1.093	1.317	0.042	0.052
E	15.773	16.327	0.621	0.631
E1	13.893	14.147	0.547	0.557
E2	3.683	3.107	0.145	0.122
E3	1.663	1.907	0.066	0.075
a	5.450		0.215	
a1	10.800		0.430	
N	3		3	
L	20.093	20.307	0.799	0.799
L1	4.186	4.472	0.164	0.175
aP	3.559	3.661	0.140	0.144
Q	5.490	5.747	0.216	0.226
S	6.043	6.297	0.238	0.248

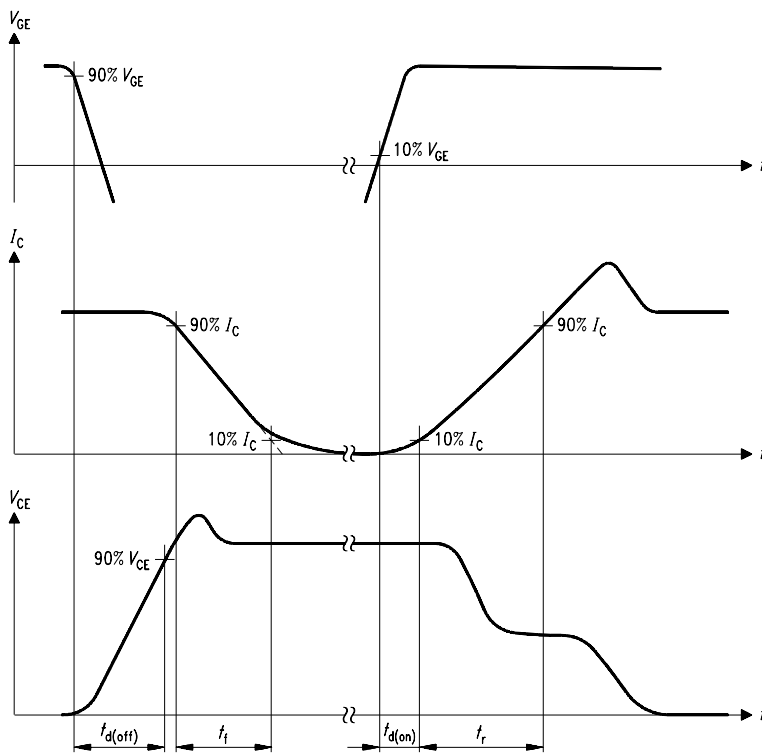


Figure A. Definition of switching times

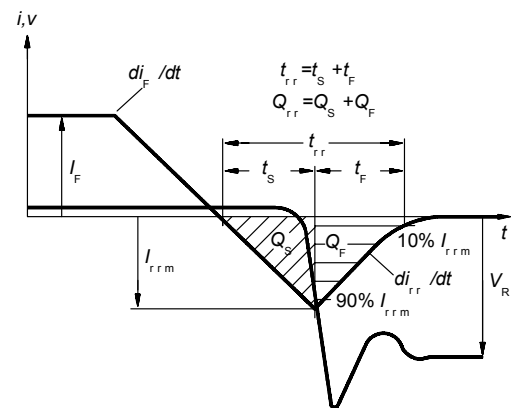


Figure C. Definition of diodes switching characteristics

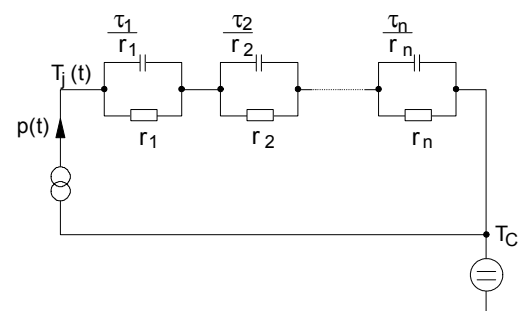


Figure D. Thermal equivalent circuit

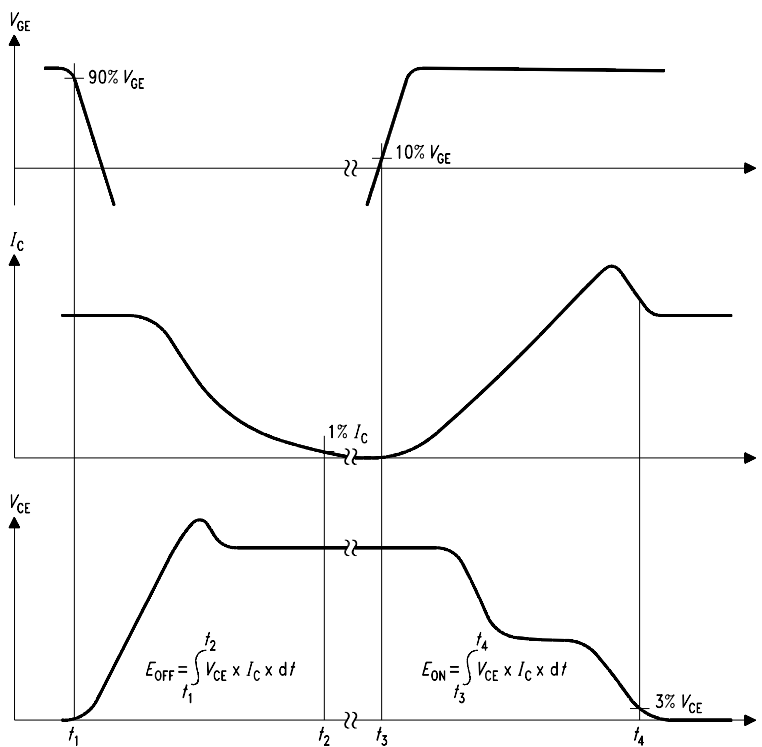


Figure B. Definition of switching losses

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